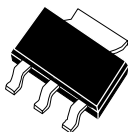


**CZTA27****NPN HIGH VOLTAGE  
DARLINGTON TRANSISTOR****Central**<sup>TM</sup>  
**Semiconductor Corp.****DESCRIPTION**

The CENTRAL SEMICONDUCTOR CZTA27 type is a NPN Silicon Darlington Transistor manufactured by the epitaxial planar process, epoxy molded in a surface mount package, designed for applications requiring extremely high gain and high voltage.

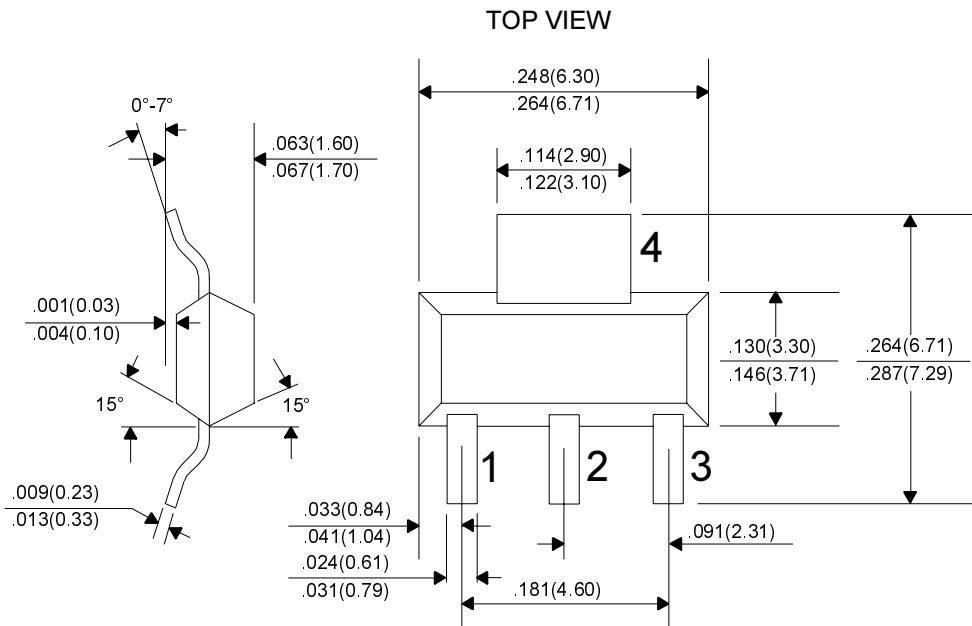
**SOT-223 CASE****MAXIMUM RATINGS** ( $T_A=25^\circ\text{C}$ )**UNITS**

Collector-Emitter Voltage	$V_{CES}$	60	V
Emitter-Base Voltage	$V_{EBO}$	10	V
Collector Current	$I_C$	500	mA
Power Dissipation	$P_D$	2.0	W
Operating and Storage Junction Temperature	$T_J, T_{stg}$	-65 to +150	$^\circ\text{C}$
Thermal Resistance	$\Theta_{JA}$	62.5	$^\circ\text{C}/\text{W}$

**ELECTRICAL CHARACTERISTICS:** ( $T_A=25^\circ\text{C}$  unless otherwise noted)

<b>SYMBOL</b>	<b>TEST CONDITIONS</b>	<b>MIN</b>	<b>MAX</b>	<b>UNITS</b>
$I_{CBO}$	$V_{CB}=50\text{V}$		100	nA
$I_{CES}$	$V_{CE}=50\text{V}$		500	nA
$I_{EBO}$	$V_{EB}=10\text{V}$		100	nA
$BV_{CBO}$	$I_C=100\mu\text{A}$	60		V
$BV_{CES}$	$I_C=100\mu\text{A}$	60		V
$V_{CE(SAT)}$	$I_C=100\text{mA}, I_B=0.1\text{mA}$		1.5	V
$V_{BE(ON)}$	$V_{CE}=5.0\text{V}, I_C=100\text{mA}$		2.0	V
$h_{FE}$	$V_{CE}=5.0\text{V}, I_C=10\text{mA}$	10,000		
$h_{FE}$	$V_{CE}=5.0\text{V}, I_C=100\text{mA}$	10,000		
$f_T$	$V_{CE}=5.0\text{V}, I_C=10\text{mA}, f=100\text{MHz}$	125		MHz

All Dimensions in Inches (mm)



**LEAD CODE:**

- 1) BASE
- 2) COLLECTOR
- 3) EMITTER
- 4) COLLECTOR